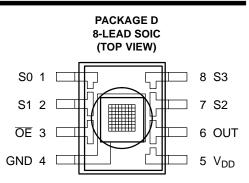


#### TCS230 PROGRAMMABLE COLOR LIGHT-TO-FREQUENCY CONVERTER

TAOS046C - AUGUST 2005

- High-Resolution Conversion of Light Intensity to Frequency
- Programmable Color and Full-Scale Output Frequency
- Communicates Directly With a Microcontroller
- Single-Supply Operation (2.7 V to 5.5 V)
- Power Down Feature
- Nonlinearity Error Typically 0.2% at 50 kHz
- Stable 200 ppm/°C Temperature Coefficient
- Low-Profile Lead (Pb) Free and RoHS Compliant Surface-Mount Package

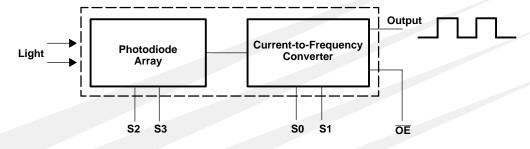


#### **Description**

The TCS230 programmable color light-to-frequency converter combines configurable silicon photodiodes and a current-to-frequency converter on single monolithic CMOS integrated circuit. The output is a square wave (50% duty cycle) with frequency directly proportional to light intensity (irradiance). The full-scale output frequency can be scaled by one of three preset values via two control input pins. Digital inputs and digital output allow direct interface to a microcontroller or other logic circuitry. Output enable  $(\overline{OE})$  places the output in the high-impedance state for multiple-unit sharing of a microcontroller input line.

The light-to-frequency converter reads an 8 x 8 array of photodiodes. Sixteen photodiodes have blue filters, 16 photodiodes have green filters, 16 photodiodes have red filters, and 16 photodiodes are clear with no filters. The four types (colors) of photodiodes are interdigitated to minimize the effect of non-uniformity of incident irradiance. All 16 photodiodes of the same color are connected in parallel and which type of photodiode the device uses during operation is pin-selectable. Photodiodes are 120  $\mu$ m x 120  $\mu$ m in size and are on 144- $\mu$ m centers.

#### **Functional Block Diagram**



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# TCS230 PROGRAMMABLE COLOR LIGHT-TO-FREQUENCY CONVERTER

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#### **Terminal Functions**

TERM	TERMINAL		DECODINE					
NAME	NO.	1/0	DESCRIPTION					
GND	4		Power supply ground. All voltages are referenced to GND.					
ŌĒ	3	I	Enable for f <sub>0</sub> (active low).					
OUT	6	0	Output frequency (f <sub>o</sub> ).					
S0, S1	1, 2	I	Output frequency scaling selection inputs.					
S2, S3	7, 8	I	Photodiode type selection inputs.					
$V_{DD}$	5		Supply voltage					

#### **Table 1. Selectable Options**

S0	S1	OUTPUT FREQUENCY SCALING (fo)	S2	S3	PHOTODIODE TYPE
L	L	Power down	L	L	Red
L	Н	2%	L	Н	Blue
Н	L	20%	Н	L	Clear (no filter)
Н	Н	100%	Н	Н	Green

#### **Available Options**

DEVICE	T <sub>A</sub>	PACKAGE – LEADS	PACKAGE DESIGNATOR	ORDERING NUMBER	
TCS230	-40°C to 85° C	SOIC-8	D	TCS230D	

### Absolute Maximum Ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage, V <sub>DD</sub> (see Note 1)	6 V
Input voltage range, all inputs, V <sub>I</sub>	
Operating free-air temperature range, T <sub>A</sub>	85°C
Storage temperature range –40°C to 8	85°C
Solder conditions in accordance with JEDEC J-STD-020A, maximum temperature	40°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND.

#### **Recommended Operating Conditions**

		MIN	NOM	MAX	UNIT
Supply voltage, V <sub>DD</sub>		2.7	5	5.5	V
High-level input voltage, V <sub>IH</sub>	V <sub>DD</sub> = 2.7 V to 5.5 V	2		$V_{DD}$	V
Low-level input voltage, V <sub>IL</sub>	V <sub>DD</sub> = 2.7 V to 5.5 V	0		8.0	V
Operating free-air temperature rang	e, T <sub>A</sub>	-40		70	°C



# Electrical Characteristics at $T_A$ = 25°C, $V_{DD}$ = 5 V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{OH}$	High-level output voltage	$I_{OH} = -4 \text{ mA}$	4	4.5		V
$V_{OL}$	Low-level output voltage	I <sub>OL</sub> = 4 mA		0.25	0.40	V
I <sub>IH</sub>	High-level input current				5	μΑ
I <sub>IL</sub>	Low-level input current				5	μΑ
	Complex compant	Power-on mode		2	3	mA
I <sub>DD</sub>	Supply current	Power-down mode		7	15	μΑ
		S0 = H, S1 = H	500	600		kHz
	Full-scale frequency (See Note 2)	S0 = H, S1 = L	100	120		kHz
		S0 = L, S1 = H	10	12		kHz
	Temperature coefficient of output frequency	$\lambda \le 700 \text{ nm}, -25^{\circ}\text{C} \le T_{A} \le 70^{\circ}\text{C}$		±200		ppm/°C
k <sub>SVS</sub>	Supply voltage sensitivity	V <sub>DD</sub> = 5 V ±10%	·	±0.5		%/V

NOTE 2: Full-scale frequency is the maximum operating frequency of the device without saturation.



# Operating Characteristics at $V_{DD}$ = 5 V, $T_A$ = 25°C, S0 = H, S1 = H (unless otherwise noted) (See Notes 3, 4, 5, 6, and 7).

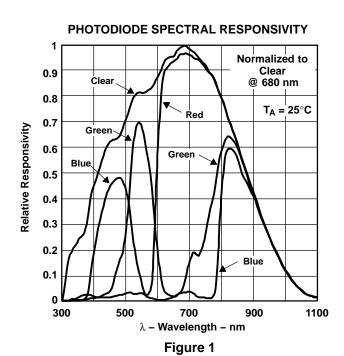
PARAMETER		TEST CONDITIONS	PHOT	LEAR TODIO H, S3	DE		BLUE OTODIO = L, S3		PHO	GREEN OTODIC = H, S3	DE		RED TODIC L, S3		UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
		$E_e = 47.2 \mu\text{W/cm}^2,$ $\lambda_p = 470 \text{nm}$	16	20	24	11.2	16.4	21.6							kHz
f <sub>O</sub>	Output frequency	$E_e = 40.4 \ \mu \text{W/cm}^2,$ $\lambda_p = 524 \ \text{nm}$	16	20	24				8	13.6	19.2				kHz
		$E_e = 34.6 \ \mu \text{W/cm}^2,$ $\lambda_p = 640 \ \text{nm}$	16	20	24							14	19	24	kHz
$f_D$	Dark frequency	E <sub>e</sub> = 0		2	12		2	12		2	12		2	12	Hz
		$\lambda_p = 470 \text{ nm}$		424			348			81			26		
٦	Irradiance	$\lambda_p = 524 \text{ nm}$		495			163			337			35		Hz/
Re	R <sub>e</sub> responsivity (Note 8)	$\lambda_p = 565 \text{ nm}$		532			37			309			91		(μW/ cm <sup>2</sup> )
		$\lambda_p = 640 \text{ nm}$		578			17			29			550		,
		$\lambda_p = 470 \text{ nm}$	,	1410			1720								
	Saturation irradiance	$\lambda_p = 524 \text{ nm}$	,	1210						1780					μW/
	(Note 9)	$\lambda_p = 565 \text{ nm}$		1130						1940					cm <sup>2</sup>
	, ,	$\lambda_p = 640 \text{ nm}$	,	1040									1090		
		$\lambda_p = 470 \text{ nm}$		565			464			108			35		
	Illuminance	$\lambda_p = 524 \text{ nm}$		95			31			65			7		Hz/
$R_v$	responsivity (Note 10)	$\lambda_p = 565 \text{ nm}$		89			6			52			15		lx
	,	$\lambda_p = 640 \text{ nm}$		373			11			19			355		
		$f_O = 0$ to 5 kHz		±0.1 %			±0.1 %			±0.1 %			±0.1 %		% F.S.
	Nonlinearity (Note 11)	f <sub>O</sub> = 0 to 50 kHz		±0.2 %			±0.2 %			±0.2 %			±0.2 %		% F.S.
		f <sub>O</sub> = 0 to 500 kHz		±0.5 %			±0.5 %			±0.5 %			±0.5 %		% F.S.
	Recovery from power down			100			100			100			100		μs
	Response time to output enable (OE)			100			100			100			100		ns

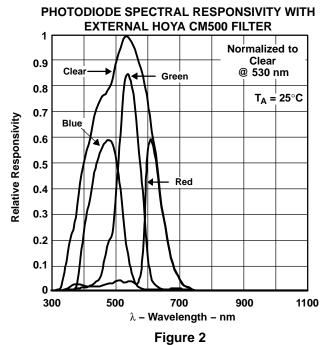
NOTES: 3. Optical measurements are made using small-angle incident radiation from a light-emitting diode (LED) optical source.

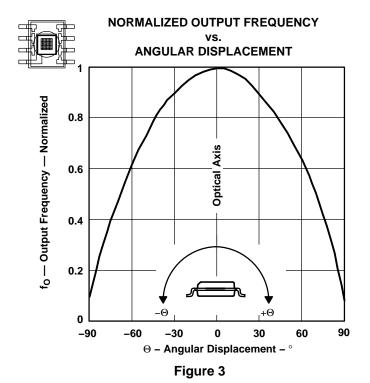
- 4. The 470 nm input irradiance is supplied by an InGaN light-emitting diode with the following characteristics: peak wavelength  $\lambda_D = 470$  nm, spectral halfwidth  $\Delta\lambda V_2 = 35$  nm, and luminous efficacy = 75 lm/W.
- 5. The 524 nm input irradiance is supplied by an InGaN light-emitting diode with the following characteristics: peak wavelength  $\lambda_p = 524$  nm, spectral halfwidth  $\Delta\lambda V_2 = 47$  nm, and luminous efficacy = 520 lm/W.
- 6. The 565 nm input irradiance is supplied by a GaP light-emitting diode with the following characteristics: peak wavelength  $\lambda_p$  = 565 nm, spectral halfwidth  $\Delta\lambda V_2$  = 28 nm, and luminous efficacy = 595 lm/W.
- 7. The 640 nm input irradiance is supplied by a AlInGaP light-emitting diode with the following characteristics: peak wavelength  $\lambda_{\rm p}$  = 640 nm, spectral halfwidth  $\Delta\lambda 1/2$  = 17 nm, and luminous efficacy = 155 lm/W.
- 8. Irradiance responsivity R<sub>e</sub> is characterized over the range from zero to 5 kHz.
- 9. Saturation irradiance = (full-scale frequency)/(irradiance responsivity).
- 10. Illuminance responsivity Rv is calculated from the irradiance responsivity by using the LED luminous efficacy values stated in notes 4, 5, and 6 and using 1 lx = 1 lm/m<sup>2</sup>.
- 11. Nonlinearity is defined as the deviation of fo from a straight line between zero and full scale, expressed as a percent of full scale.



#### TYPICAL CHARACTERISTICS







#### **APPLICATION INFORMATION**

#### Power supply considerations

Power-supply lines must be decoupled by a  $0.01-\mu F$  to  $0.1-\mu F$  capacitor with short leads mounted close to the device package.

#### Input interface

A low-impedance electrical connection between the device  $\overline{\text{OE}}$  pin and the device GND pin is required for improved noise immunity.

#### **Output interface**

The output of the device is designed to drive a standard TTL or CMOS logic input over short distances. If lines greater than 12 inches are used on the output, a buffer or line driver is recommended.

#### Photodiode type (color) selection

The type of photodiode (blue, green, red, or clear) used by the device is controlled by two logic inputs, S2 and S3 (see Table 1).

#### **Output frequency scaling**

Output-frequency scaling is controlled by two logic inputs, S0 and S1. The internal light-to-frequency converter generates a fixed-pulsewidth pulse train. Scaling is accomplished by internally connecting the pulse-train output of the converter to a series of frequency dividers. Divided outputs are 50%-duty cycle square waves with relative frequency values of 100%, 20%, and 2%. Because division of the output frequency is accomplished by counting pulses of the principal internal frequency, the final-output period represents an average of the multiple periods of the principle frequency.

The output-scaling counter registers are cleared upon the next pulse of the principal frequency after any transition of the S0, S1, S2, S3, and  $\overline{\text{OE}}$  lines. The output goes high upon the next subsequent pulse of the principal frequency, beginning a new valid period. This minimizes the time delay between a change on the input lines and the resulting new output period. The response time to an input programming change or to an irradiance step change is one period of new frequency plus 1  $\mu$ S. The scaled output changes both the full–scale frequency and the dark frequency by the selected scale factor.

The frequency-scaling function allows the output range to be optimized for a variety of measurement techniques. The scaled-down outputs may be used where only a slower frequency counter is available, such as low-cost microcontroller, or where period measurement techniques are used.

#### Measuring the frequency

The choice of interface and measurement technique depends on the desired resolution and data acquisition rate. For maximum data-acquisition rate, period-measurement techniques are used.

Output data can be collected at a rate of twice the output frequency or one data point every microsecond for full-scale output. Period measurement requires the use of a fast reference clock with available resolution directly related to reference clock rate. Output scaling can be used to increase the resolution for a given clock rate or to maximize resolution as the light input changes. Period measurement is used to measure rapidly varying light levels or to make a very fast measurement of a constant light source.

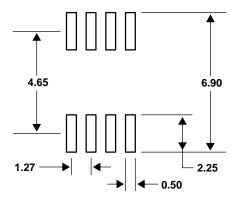
Maximum resolution and accuracy may be obtained using frequency-measurement, pulse-accumulation, or integration techniques. Frequency measurements provide the added benefit of averaging out random- or high-frequency variations (jitter) resulting from noise in the light signal. Resolution is limited mainly by available counter registers and allowable measurement time. Frequency measurement is well suited for slowly varying or constant light levels and for reading average light levels over short periods of time. Integration (the accumulation of pulses over a very long period of time) can be used to measure exposure, the amount of light present in an area over a given time period.



#### **APPLICATION INFORMATION**

## **PCB Pad Layout**

Suggested PCB pad layout guidelines for the D package are shown in Figure 4.



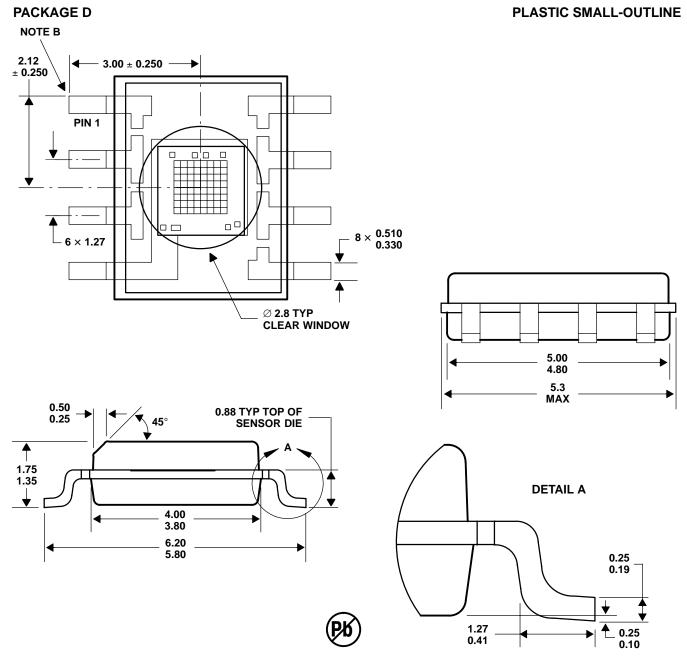
NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

Figure 4. Suggested D Package PCB Layout

#### **MECHANICAL INFORMATION**

This SOIC package consists of an integrated circuit mounted on a lead frame and encapsulated with an electrically nonconductive clear plastic compound. The TCS230 has an  $8\times8$  array of photodiodes with a total size of 1.15 mm by 1.15 mm. The photodiodes are 120  $\mu$ m  $\times$  120  $\mu$ m in size and are positioned on 144  $\mu$ m centers.



- NOTES: A. All linear dimensions are in millimeters.
  - B. The center of the 1.15-mm by 1.15-mm photo-active area is referenced to the upper left corner tip of the lead frame (Pin 1).
  - C. Package is molded with an electrically nonconductive clear plastic compound having an index of refraction of 1.55.
  - D. This drawing is subject to change without notice.

Figure 5. Package D — Plastic Small Outline IC Packaging Configuration



Max -5°C/sec

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#### MANUFACTURING INFORMATION

The Plastic Small Outline IC package (D) has been tested and has demonstrated an ability to be reflow soldered to a PCB substrate.

The solder reflow profile describes the expected maximum heat exposure of components during the solder reflow process of product on a PCB. Temperature is measured on top of component. The component should be limited to a maximum of three passes through this solder reflow profile.

PARAMETER	REFERENCE	TCS230
Average temperature gradient in preheating		2.5°C/sec
Soak time	t <sub>soak</sub>	2 to 3 minutes
Time above 217°C	t <sub>1</sub>	Max 60 sec
Time above 230°C	t <sub>2</sub>	Max 50 sec
Time above T <sub>peak</sub> –10°C	t <sub>3</sub>	Max 10 sec
Peak temperature in reflow	T <sub>peak</sub>	240° C (-0°C/+5°C)

Table 2. TCS230 Solder Reflow Profile

Temperature gradient in cooling

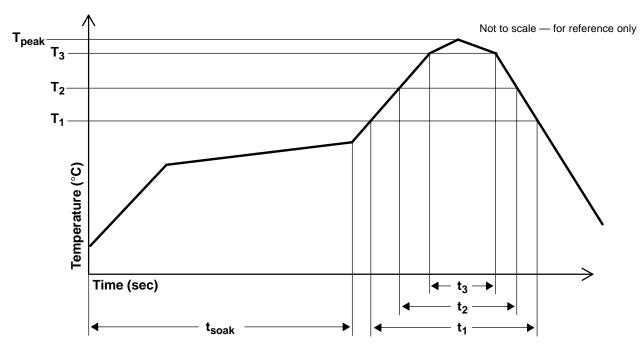


Figure 6. TCS230 Solder Reflow Profile Graph

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